

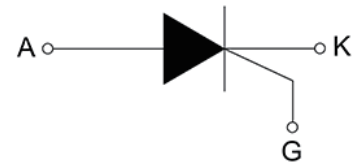
DESCRIPTION:

With high ability to withstand the shock loading of large current, chip series of silicon controlled rectifiers provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	≤ 5	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}\text{C}$
Operating junction temperature range	T_j	-40-125	$^{\circ}\text{C}$
Repetitive peak off-state voltage ($T_j=25^{\circ}\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^{\circ}\text{C}$)	V_{RRM}	600	V
Average on-state current ($T_c \leq 86^{\circ}\text{C}$)	$I_{T(AV)}$	7.6	A
RMS on-state current ($T_c \leq 86^{\circ}\text{C}$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}$, $T_j=25^{\circ}\text{C}$)	I_{TSM}	140	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}$, $T_j=25^{\circ}\text{C}$)		154	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^{\circ}\text{C}$)	I^2t	98	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^{\circ}\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$

Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	-	5	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ C$ $R_L=3.3k\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	30	mA
I_H	$I_T=500mA$	-	-	15	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125^\circ C$	400	-	-	V/ μs
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25^\circ C$	-	5	-	μs
t_{off}		-	80	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=24A$ $t_p=380\mu s$	$T_j=25^\circ C$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ C$	0.8	V
R_D	Dynamic resistance	$T_j=125^\circ C$	27	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	5	μA
I_{RRM}		$T_j=125^\circ C$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case(DC)	2.5	$^\circ C/W$
$R_{th(j-a)}$	junction to ambient (DC)	70	$^\circ C/W$

FIG : Maximum power dissipation versus RMS on-state current

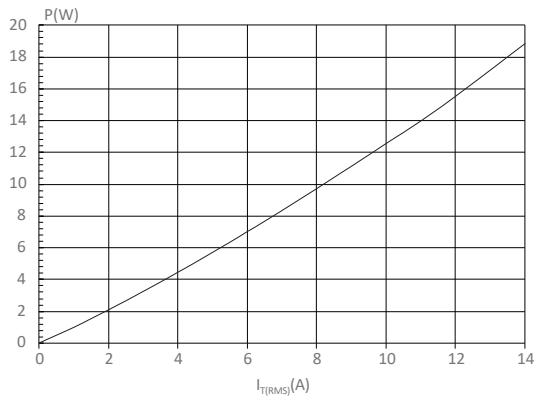


FIG : RMS on-state current versus case temperature

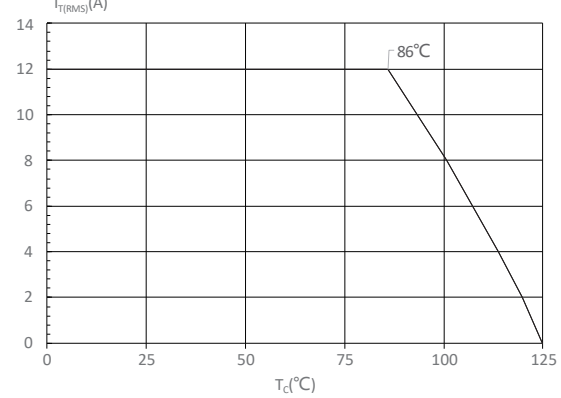


FIG : Surge peak on-state current versus number of cycles

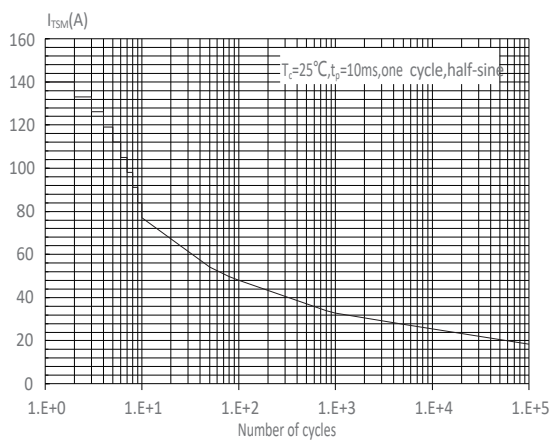


FIG : On-state characteristics

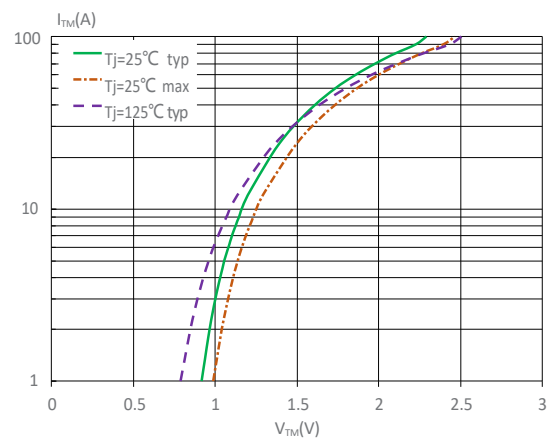


FIG : Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

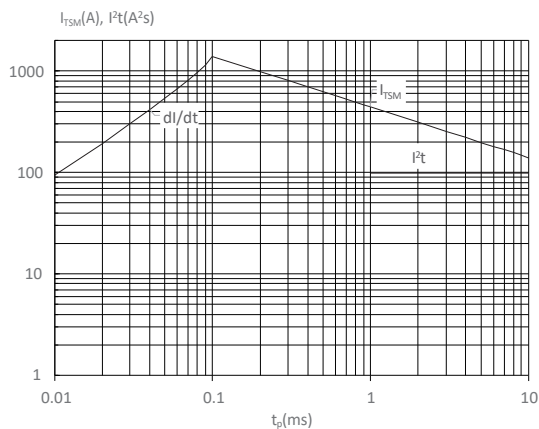


FIG : Relative variations of gate trigger current, holding current and latching current versus junction temperature

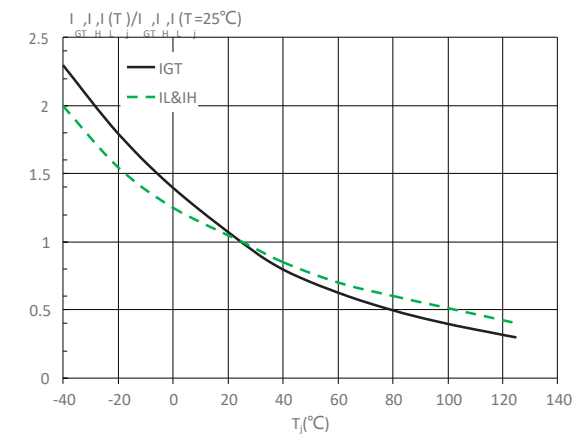
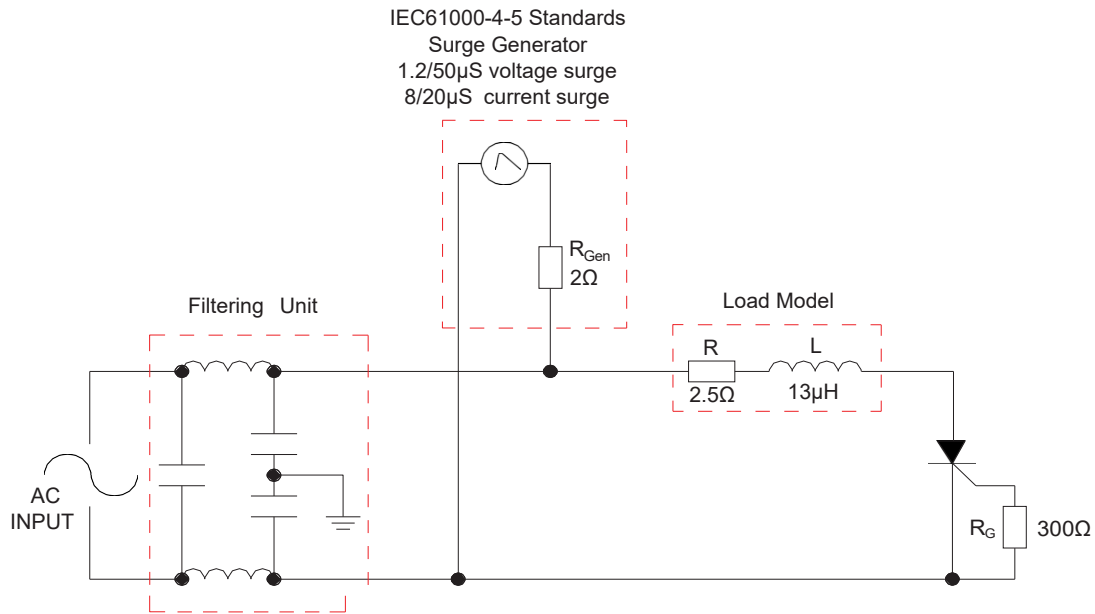


FIG : Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.